

ZXTN2018F

60V, SOT23, NPN medium power transistor

Summary

$V_{(BR)CEV} > 140V$, $V_{(BR)CEO} > 60V$

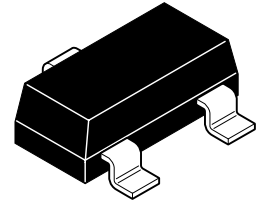
$I_{C(cont)} = 5A$

$R_{CE(sat)} = 25\ m\Omega$ typical

$V_{CE(sat)} < 45\ mV$ @ 1A

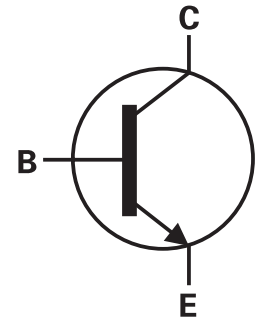
$P_D = 1.2W$

Complementary part number : ZXTP2027F



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

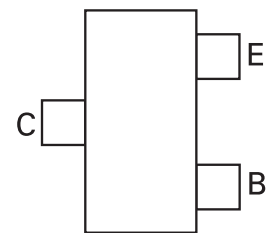


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 140V forward blocking voltage

Applications

- MOSFET and IGBT gate driving
- Motor drive
- Relay, lamp and solenoid drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN2018FTA	7	8	3,000

Device marking

851

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	140	V
Collector-emitter voltage	$V_{(BR)CEV}$	140	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	7	V
Peak pulse current	I_{CM}	12	A
Continuous collector current ^(a)	I_C	5	A
Base current	I_B	1	A
Power dissipation @ $T_A=25^{\circ}C$ ^(a)	P_D	1.0	W
Linear derating factor		8.0	mW/ $^{\circ}C$
Power dissipation @ $T_A=25^{\circ}C$ ^(b)	P_D	1.2	W
Linear derating factor		9.6	mW/ $^{\circ}C$
Power dissipation @ $T_A=25^{\circ}C$ ^(c)	P_D	1.56	W
Linear derating factor		12.5	mW/ $^{\circ}C$
Operating and storage temperature	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	125	$^{\circ}C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	104	$^{\circ}C/W$
Junction to ambient ^(c)	$R_{\theta JA}$	80	$^{\circ}C/W$

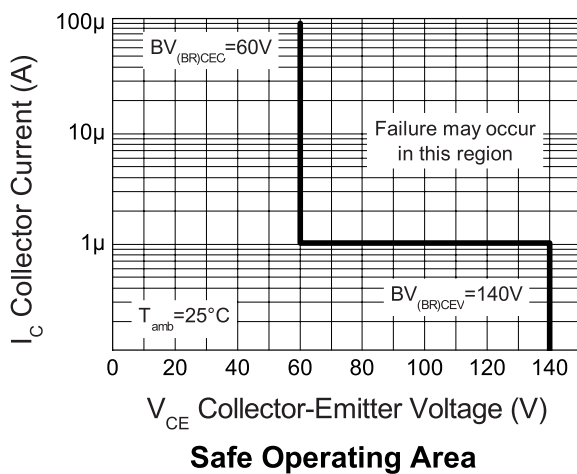
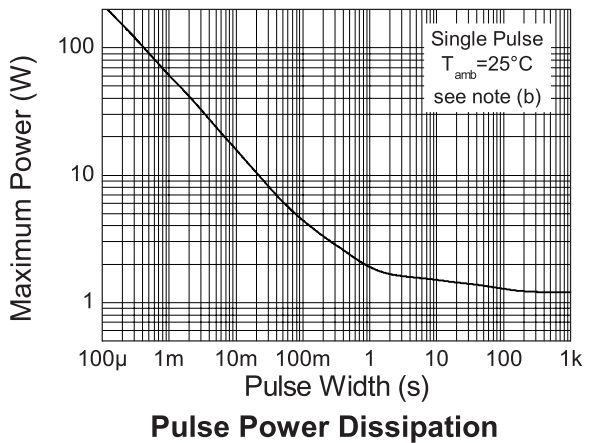
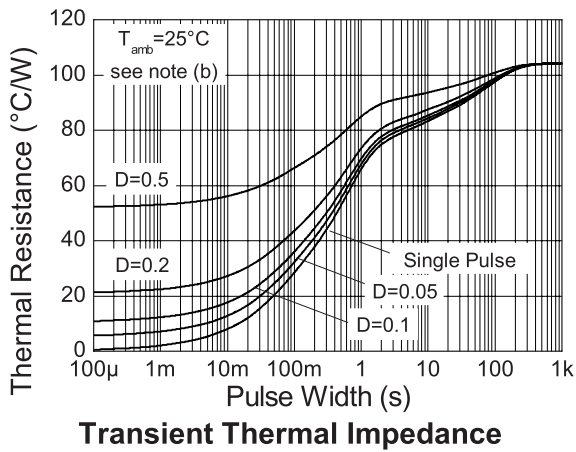
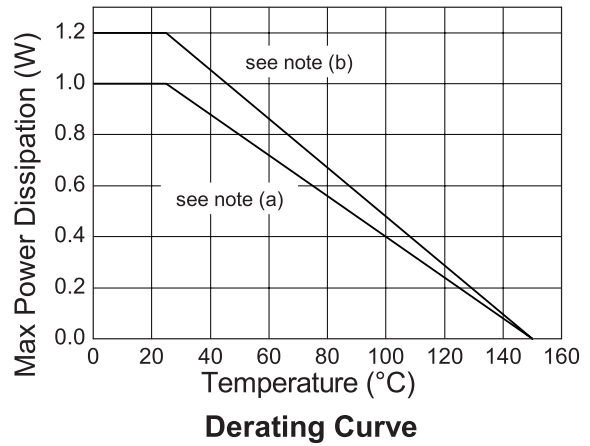
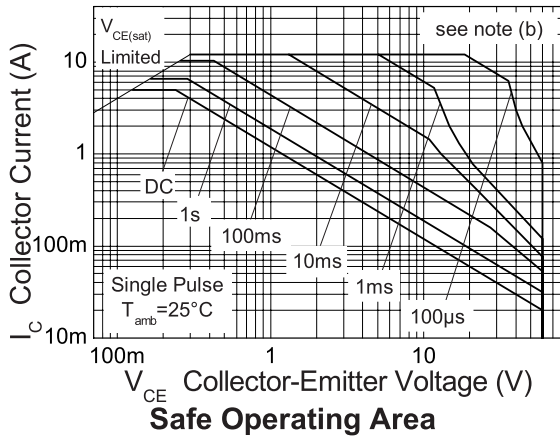
NOTES:

(a) Mounted on 18mm x 18mm X 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(b) Mounted on 30mm x 30mm X 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions.

(c) as (b) above measured at $t < 5$ secs.

Characteristics



ZXTN2018F

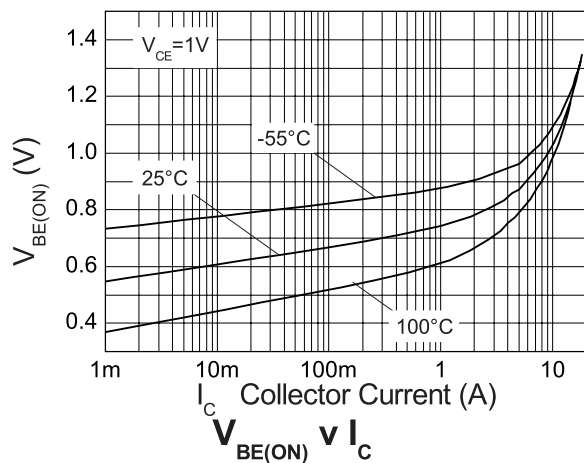
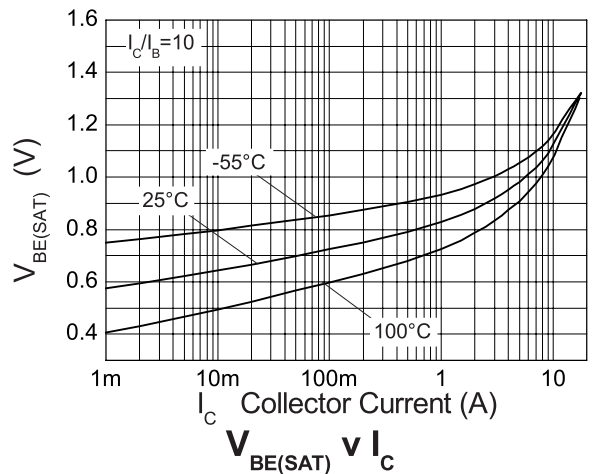
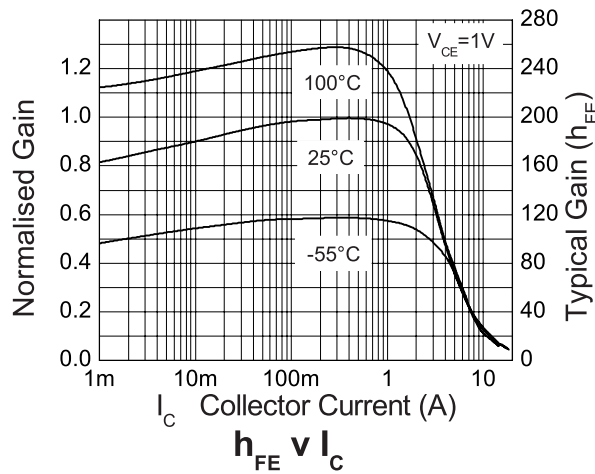
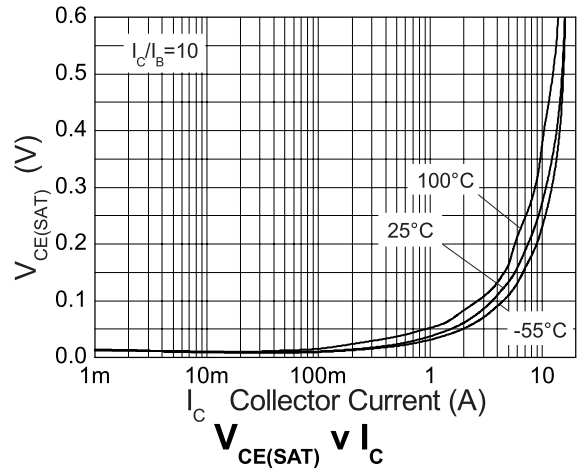
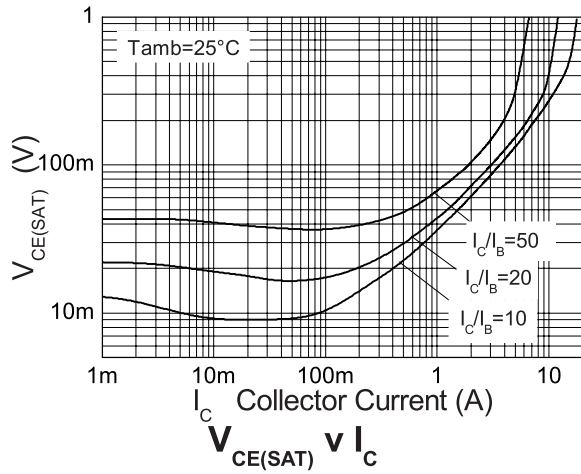
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	140	180		V	$I_C=100\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(BR)CEV}$	140	180		V	$I_C=1\mu\text{A}$, $-1\text{V} < V_{BE} < +0.3\text{V}$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	60	80		V	$I_C=10\text{mA}$ ^(a)
Emitter-base breakdown voltage	$V_{(BR)EBO}$	7	8		V	$I_E=100\mu\text{A}$
Collector-emitter cut-off current	I_{CEV}		<1	20	nA	$V_{CE}=110\text{V}$, $V_{BE} = -1\text{V}$
Collector-base cut-off current	I_{CBO}		<1	20	nA	$V_{CB}=110\text{V}$
Emitter-base cut-off current	I_{EBO}		<1	10	nA	$V_{EB}=6\text{V}$
Static forward current transfer ratio	H_{FE}	100 100 40 15	220 200 65 25	300		$I_C=10\text{mA}$, $V_{CE}=1\text{V}^{(a)}$ $I_C=2\text{A}$, $V_{CE}=1\text{V}^{(a)}$ $I_C=5\text{A}$, $V_{CE}=1\text{V}^{(a)}$ $I_C=10\text{A}$, $V_{CE}=1\text{V}^{(a)}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		15 35 40 85 145 170	30 45 55 110 170 210	mV mV mV mV mV mV	$I_C=0.1\text{A}$, $I_B=5\text{mA}^{(a)}$ $I_C=1\text{A}$, $I_B=100\text{mA}^{(a)}$ $I_C=1\text{A}$, $I_B=50\text{mA}^{(a)}$ $I_C=2\text{A}$, $I_B=50\text{mA}^{(a)}$ $I_C=5\text{A}$, $I_B=250\text{mA}^{(a)}$ $I_C=6\text{A}$, $I_B=300\text{mA}^{(a)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		0.92	1.00	V	$I_C=5\text{A}$, $I_B=250\text{mA}^{(a)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		0.85	0.95	V	$I_C=5\text{A}$, $V_{CE}=1\text{V}^{(a)}$
Transition frequency	f_T		130		MHz	$I_C=100\text{mA}$, $V_{CE}=10\text{V}$, $f=50\text{MHz}$
Output capacitance	C_{obo}		28		pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$
Turn-on time	$t_{(on)}$		33		ns	$V_{CC}=10\text{V}$, $I_C=1\text{A}$,
Turn-off time	$t_{(off)}$		668		ns	$I_{B1}=I_{B2}=100\text{mA}$

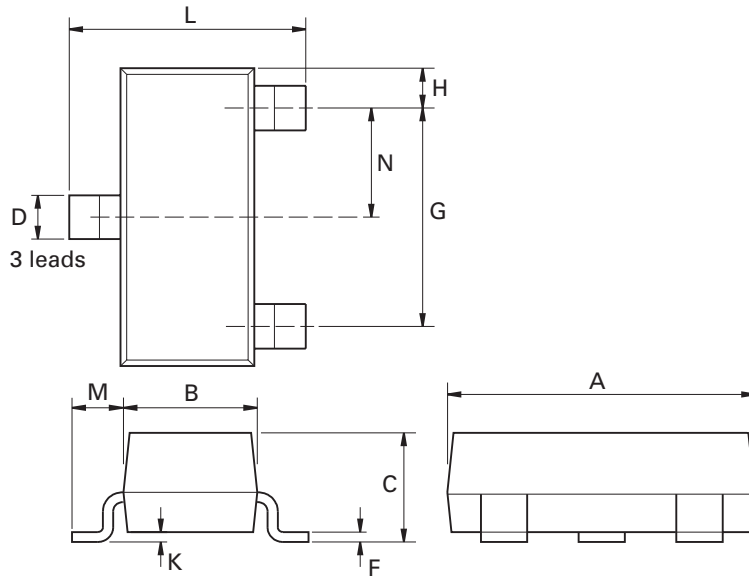
NOTES:

(a) Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.

Typical characteristics



Packaging details - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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